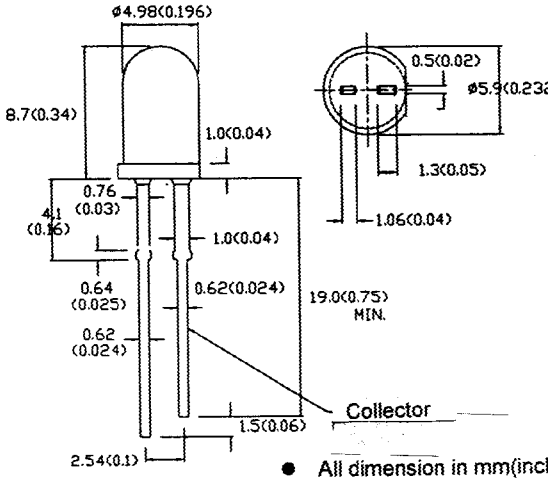
MICRO ELECTRONICS

NPN SILICON
PHOTO-TRANSISTOR

DESCRIPTION

The MEL79D is NPN silicon planar photo-transistor with 5mmΦlight rejective filter epoxy package. It features ultra high illumination sensitivity and fast response time.



- All dimension in mm(incl
- No Scale
- Tol. : +/-0.3mm

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	VCEO	30
Emitter-Collector Voltage	VECO	5
Continuous Power Dissipation (Ta=25°C)	Pd	50m
Operating Junction Temperature	Tj	-40 to +85°
Storage Temperature Range	Tstg	-40 to +100°

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BVCEO	30		V	IC=100μA Ee=0
Emitter-Collector Breakdown Voltage	BVECO	5		V	IC=100μA Ee=0
Dark Current	ID		200	nA	VCE=10V Ee=0
Light Current	IL	4		mA	VCE=5V Ee=5mW/cm^2*
Collector-Emitter Saturation Voltage	VCE(sat)		0.3	V	IC=500μA Ee=20mW/cm^2
Rise Time	Tr	3	TYP	μS	Vcc=5V IC=4mA RL=100
Fall Time	Tf	3	TYP	μS	Vcc=5V IC=4mA RL=100

* Measured at noted irradiance as emitted from tungstun filament lamp at a colo temperature of 2854°K.

MICRO ELECTRONICS LTD. 美科有限公司
38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 341 0321 Telex: 43510 Micro Hx. Tel: 343 0181-5